

Form PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Specimen)

CS-01-111

Application Number

10/676,896

Applicant

Vincent Ho et al.

Filing Date

10/01/03

Draw Art Unit

28/3

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	ALING DATE IF APPROPRIATE
CC	6128243	10/3/00	Chen et al.	365	227	12/3/99
CC	5783498	7/21/98	Dotta	438	778	5/28/96
CC	6060743	5/9/00	Sugiyama et al.	257	321	5/20/98
CC	6090666	7/18/00	Ueda et al.	438	257	9/30/98
CC	6656792	12/10/03	Choi et al.	438	257	3/1/02

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portmanteau Pages, Etc.)

CC -	Ya-Chin King et al., "MOS Memory Using Germanium Nanocrystals Formed by Thermal Oxidation of Si _{1-x} Ge _x ", IEDM Techn. Digest, 1998, pp. 115-118.
CC -	"A Silicon Nanocrystals Based Memory", Tiwari et al., Appl. Phys. Lett. 68(10), pp. 1377-1379, March 4, 1996

EXAMINER

Chandra Chaudhari

DATE CONSIDERED

1-05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.